

**Supporting Information
for
“A Combined First Principles and Experimental Approach to
 Bi_2WO_6 ”**

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I. XRD ANALYSIS

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Sample/DFT		Crystallographic Parameters, Bond Lengths and Bond Angles						$d_{\text{Bi}_2\text{O}_3}$ (Å)	χ^2	
Sym.	a (Å)	b (Å)	c (Å)	α (°)	β (°)	γ (°)	V (Å ³)	$d_{\text{W-O}}$ (Å)		
SBWO	$Pca2_1$ 5.433 16.415 5.454	90	90	486.442	1797	1.803	1.859	2.182	2.242	2.302
HBWO-U	$Pca2_1$ 5.449 16.348 5.450	90	90	485.487	1799	1.862	2.135	2.441	2.498	2.500
HBWO-S	$Pca2_1$ 5.452 16.340 5.440	90	90	484.601	1797	1.806	1.853	2.180	2.241	2.300
GGA-PBE	$Pca2_1$ 5.551 16.882 5.591	90	90	523.938	1812	1.854	2.133	2.146	2.434	2.498
GGA-PBE+ U_d (2 eV)+ U_p (2 eV)	$Pca2_1$ 5.515 16.979 5.558	90	90	520.393	1895	1.889	2.204	2.216	1.887	2.142
GGA-PBE+ U_d (5 eV)+ U_p (5 eV)	$Pca2_1$ 5.468 17.111 5.514	90	90	515.931	1895	1.903	2.021	2.027	1.922	1.9898
GGA-PBE+ U_d (7 eV)+ U_p (7 eV)	$Pca2_1$ 5.438 11.7.206 5.488	90	90	513.416	1895	1.901	1.902	1.831	1.846	1.893
GGA-PBE+ U_d (9 eV)+ U_p (9 eV)	$Pca2_1$ 5.422 17.263 5.477	90	90	512.634	1895	1.901	1.902	1.864	1.887	1.900
GGA-PBE+ U_d (12 eV)+ U_p (12 eV)	$Pca2_1$ 5.408 17.340 5.478	90	90	513.716	1895	1.903	2.021	2.027	1.926	1.987
GGA-PBE+ U_d (14 eV)+ U_p (14 eV)	$Pca2_1$ 5.401 17.404 5.482	90	90	515.284	1895	1.901	1.902	1.952	1.964	1.974

TABLE S1. Crystallographic parameters of SBWO, HBWO-U, and HBEO-S samples along with that of GGA-PBE and GGA-PBE+ U_d + U_p for different values of U_d and U_p .

Crystallographic Parameters, Bond Lengths and Bond Angles										
Sample/DFT	$a(\text{\AA})$	$b(\text{\AA})$	$c(\text{\AA})$	$\alpha(^{\circ})$	$\beta(^{\circ})$	$\gamma(^{\circ})$	$V(\text{\AA}^3)$	$d_{\text{W-O}}(\text{\AA})$	$d_{\text{Bi-O}}(\text{\AA})$	χ^2
SBWO	$Pca2_1$	5.43316.4155.454	90	90	486.442	1.797	1.803	1.8592.182	2.242	2.3021.75
HBWO-U	$Pca2_1$	5.44916.3485.450	90	90	485.487	1.799	1.862	2.135	2.1442.441	2.498
HBWO-S	$Pca2_1$	5.45216.3405.440	90	90	484.601	1.797	1.806	1.8532.180	2.241	2.3001.45
GGA-PBE+vdW	$Pca2_1$	5.50816.6165.517	90	90	504.921	1.819	1.855	2.135	2.1472.438	2.500
GGA-PBE+ U_d (2 eV)+ U_p (2 eV)+vdW	$Pca2_1$	5.48316.6675.488	90	90	501.493	1.835	1.888	2.133	2.1522.434	2.498
GGA-PBE+ U_d (5 eV)+ U_p (5 eV)+vdW	$Pca2_1$	5.44016.8005.451	90	90	498.105	1.869	1.888	2.114	2.1142.485	2.492
GGA-PBE+ U_d (7 eV)+ U_p (7 eV)+vdW	$Pca2_1$	5.41616.8685.432	90	90	496.2161	1.898	1.888	2.114	2.1142.485	2.492
GGA-PBE+ U_d (9 eV)+ U_p (9 eV)+vdW	$Pca2_1$	5.40416.9135.425	90	90	495.7781	1.900	1.895	2.114	2.1142.485	2.492
GGA-PBE+ U_d (12 eV)+ U_p (12 eV)+vdW	$Pca2_1$	5.39316.9635.425	90	90	496.2591	1.902	1.902	2.114	2.1142.485	2.492
GGA-PBE+ U_d (14 eV)+ U_p (14 eV)+vdW	$Pca2_1$	5.38717.0075.425	90	90	497.0511	1.895	1.932	2.114	2.1142.485	2.492
							1.904	1.958	2.114	2.1142.485
							1.904	1.958	2.114	2.1142.485
							1.935	1.956	2.114	2.1142.485

TABLE S2. Crystallographic parameters of SBWO, HBWO-U, and HBEO-S samples along with that of GGA-PBE+vdW and GGA-PBE+ U_d + U_p +vdW for different values of U_d and U_p . The van der Waals (vdW) interaction was included with the DFT-D3 method including Becke-Johnson (BJ) damping.

II. RAMAN ANALYSIS

TABLE S3. RT experimental Raman peaks of SBWO, HBWO-U, and HBWO-S samples along with that of DFT (GGA-PBE and GGA-PBE+ U_d+U_p) simulations. ELM: External Lattice Mode, AD: Asymmetric Distortion, SBV: Symmetric Bending Vibrations, ABV: Asymmetric Bending Vibrations, TM: Translational Mode, ABrM: Asymmetric Bridging Mode, AST: Asymmetric Stretching.

Raman Peak Analysis							
SBWO	HBWO-U	HBWO-S	GGA-PBE	GGA-PBE+ U_d+U_p	Symm.	Peak	Assignment
(cm ⁻¹)							
-	129	139	129	128	E_g	ELM	
153	152	152	154	158	A_{1g}	ELM	
-	222	225	222	228	B_{1g}	WO ₆ AD	
242	255	260	254	260	A_{1g}	Bi-O SBV	
283	282	283	274	282	E_g	WO ₆ ABV	
295	300	306	296	298	E_g	Bi ³⁺ and WO ₆ ⁶⁻ TM	
406	413	417	408	412	E_g	WO ₆ ABV	
711	716	704	713	716	B_{1g}	WO ₆ ABrM	
-	-	724	731	732	B_{1g}	O-W-O AST	
800	796	796	794	804	B_{1g}	WO ₆ ABrM	
-	814	821	811	834	B_{1g}	O-W-O AST	

III. FTIR ANALYSIS

TABLE S4. The SBWO, HBWO-U, and HBWO-S samples' FTIR peak designations to corresponding atomic motion along with DFT-derived peaks of phonon density of states for GGA-PBE+vdW and GGA-PBE+ U_d+U_p+vdW . SV: Symmetric Vibration, AST: Asymmetric Stretching, SST: Symmetric Stretching, BV: Bending Vibration.

FTIR Peak Analysis						
SBWO	HBWO-U	HBWO-S	GGA-PBE+vdW	GGA-PBE+ U_d+U_p+vdW	(cm ⁻¹)	Peak Assignment
(cm ⁻¹)						
417	427	427	419	424		Bi-O SST
533	565	565	526	540		Bi-O-Bi AST
680	703	697	684	678		W-O SST
818	812	820	782	814		Bi-O SST
958	-	-	915	930		O-H BV
1056	1026	1029	-	-		W-O SST
-	1108	-	-	-		C-C SST
-	1314	1392	-	-		C=O SST
-	1636	1627	-	-		O-H SST
3471	3469	-	-	-		O-H BV

IV. EDX ANALYSIS

The EDX spectra in Fig. S1 presents the characteristic peaks of X-ray radiation for Bi ($L_\alpha = 10.79$ keV, $L_\beta = 13.00$ keV, $M_\alpha = 2.42$ keV, W ($L_\alpha = 8.25$ keV, $L_\beta = 9.75$ keV, and $M_\alpha = 1.85$ keV) in all samples.

TABLE S5. Chemical species identification, atomic percentage at. (%) and weight percentage wt. (%) concentration analysis using EDX (Model: EDAX Team) of SBWO, HBWO-U, and HBWO-S.

EDX Analysis					
Sample	Element	at. (%) (Theory)	at. (%) (Exp.)	wt. (%) (Theory)	wt. (%) (Exp.)
SBWO	Bi	22.22	22.8	59.89	59
	W	11.11	10.79	26.35	27.31
	O	66.67	66.41	13.76	13.69
HBWO-U	Bi	22.22	22.39	59.89	59.89
	W	11.11	11.12	26.35	26.66
	O	66.67	66.49	13.76	13.45
HBWO-S	Bi	22.22	22.16	59.89	59.9
	W	11.11	11.37	26.35	26.38
	O	66.67	66.47	13.76	13.72

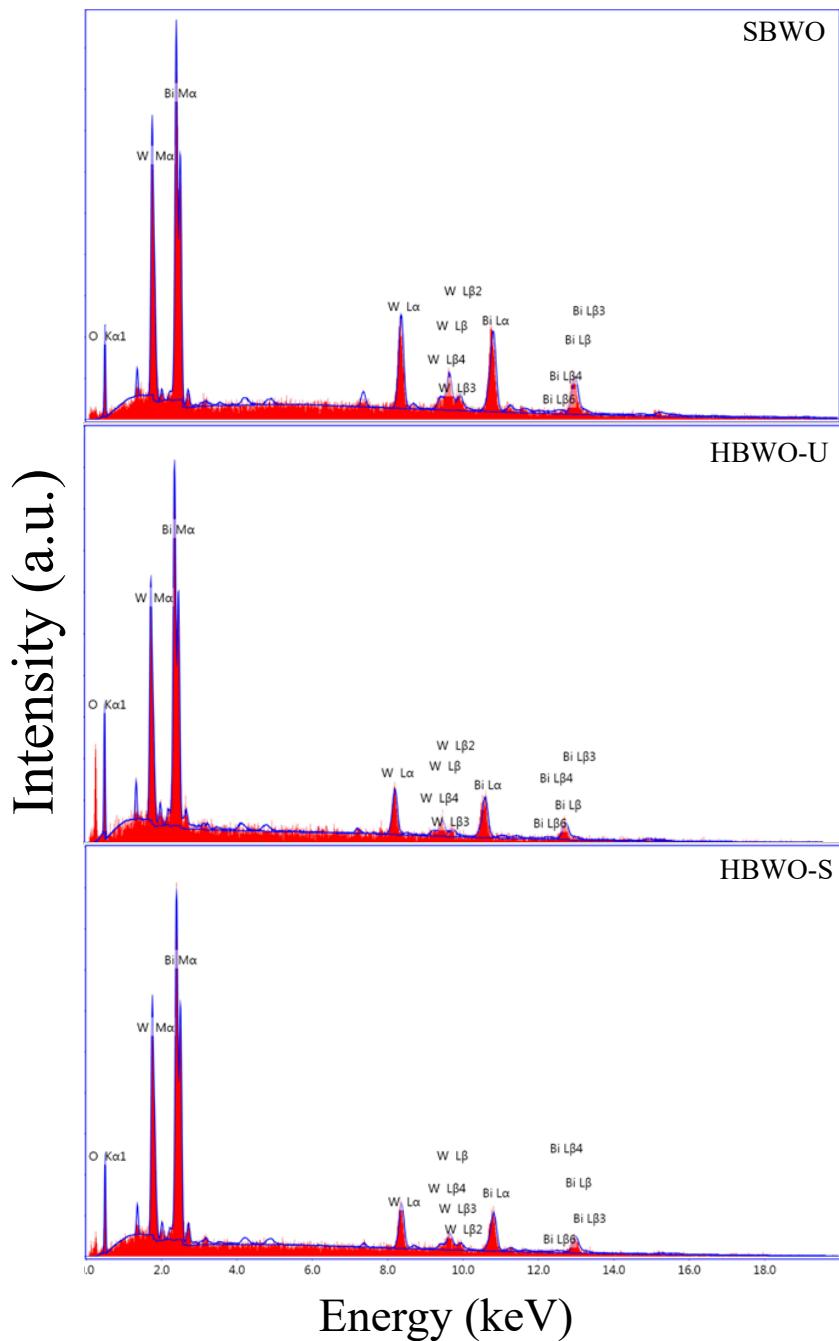


FIG. S1. EDX spectra of (a) SBWO, (b) SBWO-U, and (c) SBWO-S measured by EDX Model: EDAX Team machine.

V. ELECTRONIC PROPERTIES SIMULATION

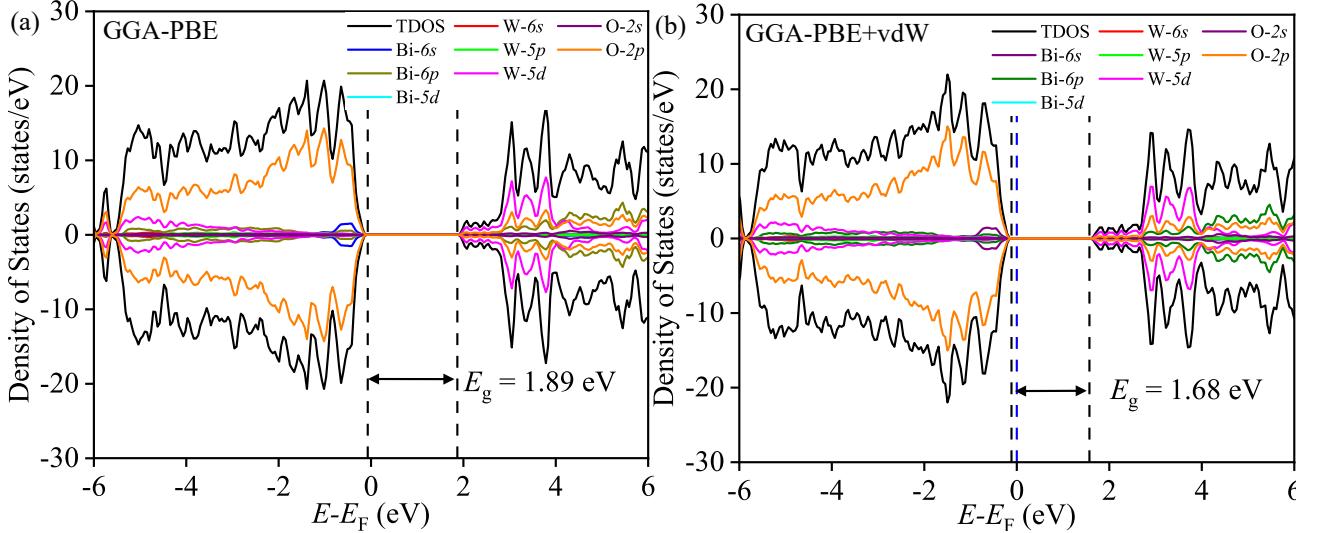


FIG. S2. TDOS and PDOS of BWO for (a) GGA-PBE and (b) GGA-PBE+vdW functionals. The inclusion of vdW force reduces the band gap E_g in DOS.

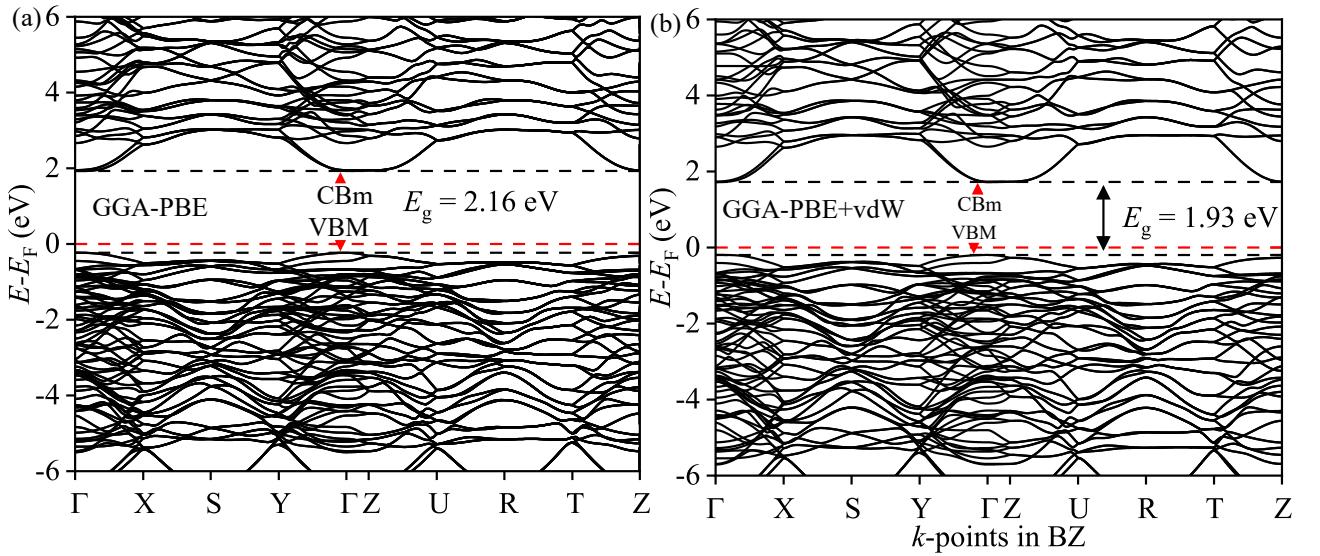


FIG. S3. Electronic BS of BWO for (a) GGA-PBE and (b) GGA-PBE+vdW functionals. The inclusion of vdW force reduces the band gap E_g in BS. The GGA-PBE predicts the erroneous direct nature of the band gap regardless of the vdW force.

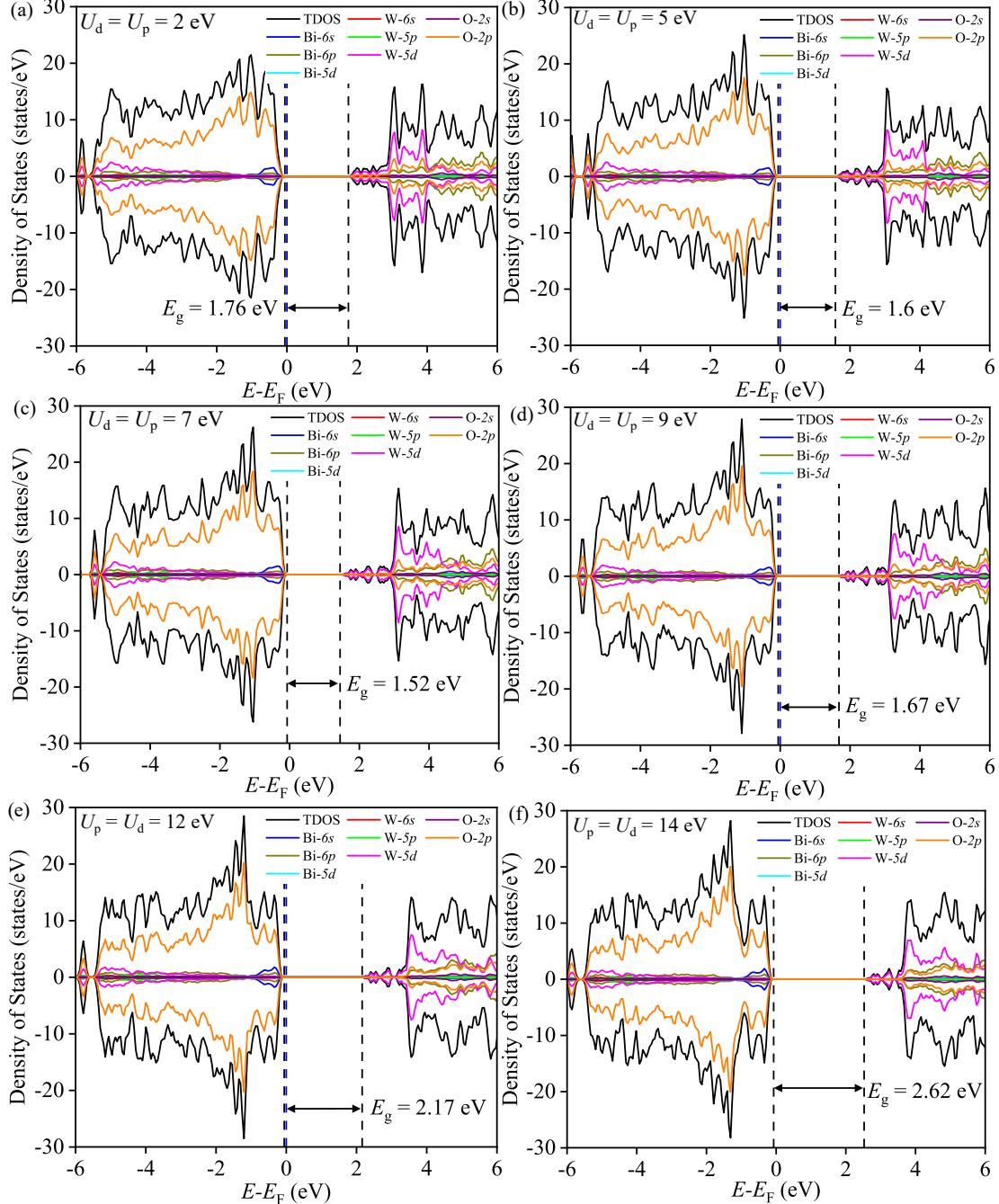


FIG. S4. TDOS and PDOS of BWO for GGA-PBE+ U_d+U_p with (a) $U_d = U_p = 2$ eV, (b) $U_d = U_p = 5$ eV, (c) $U_d = U_p = 7$ eV, (d) $U_d = U_p = 9$ eV, (e) $U_d = U_p = 12$ eV and (f) $U_d = U_p = 14$ eV. The band gap E_g varies with different values of U_d and U_p .

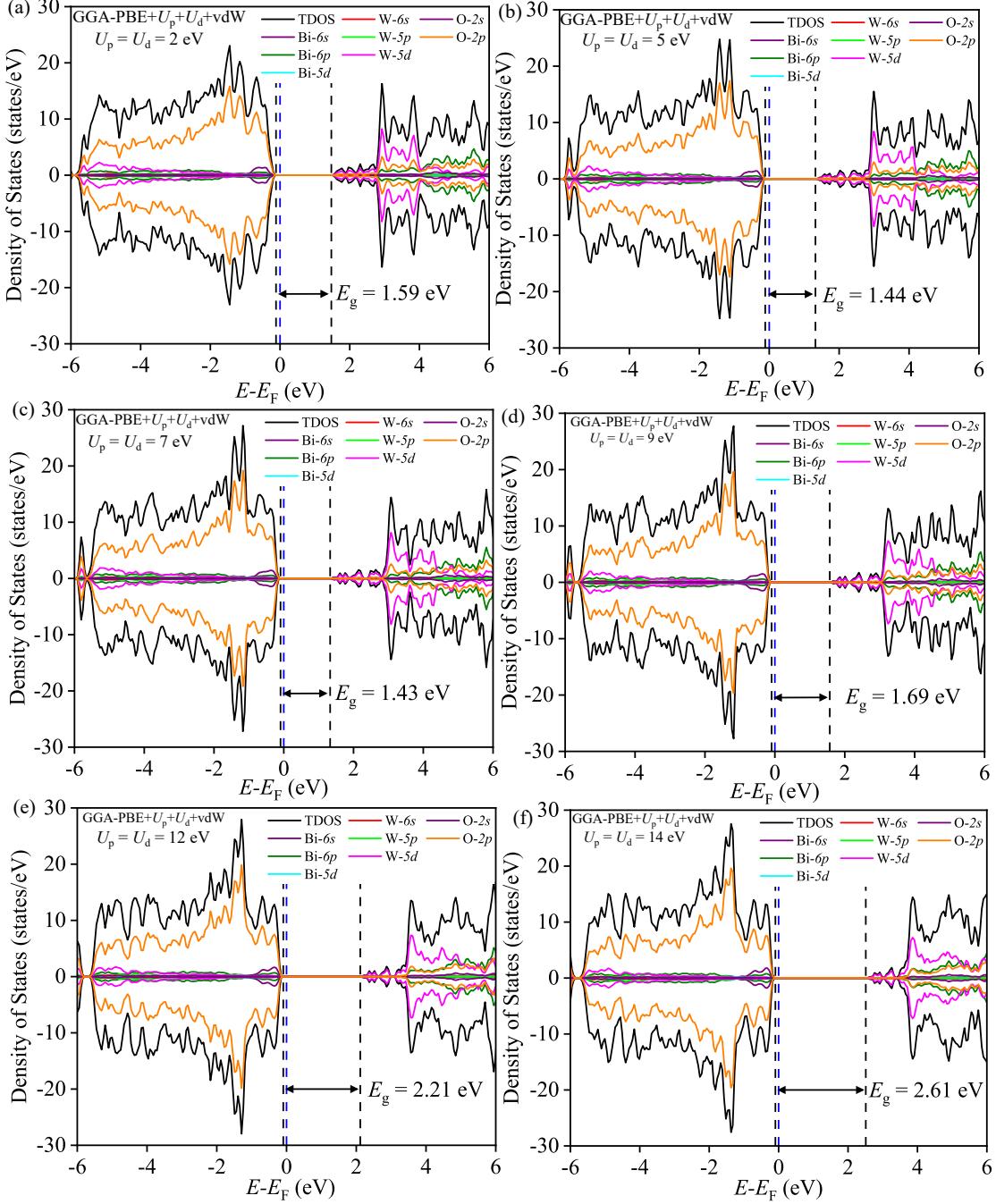


FIG. S5. The vdW force is included. TDOS and PDOS of BWO for GGA-PBE+ U_d+U_p+vdW with (a) $U_d = U_p = 2$ eV, (b) $U_d = U_p = 5$ eV, (c) $U_d = U_p = 7$ eV, (d) $U_d = U_p = 9$ eV, (e) $U_d = U_p = 12$ eV and (f) $U_d = U_p = 14$ eV. The band gap E_g varies with different values of U_d and U_p .

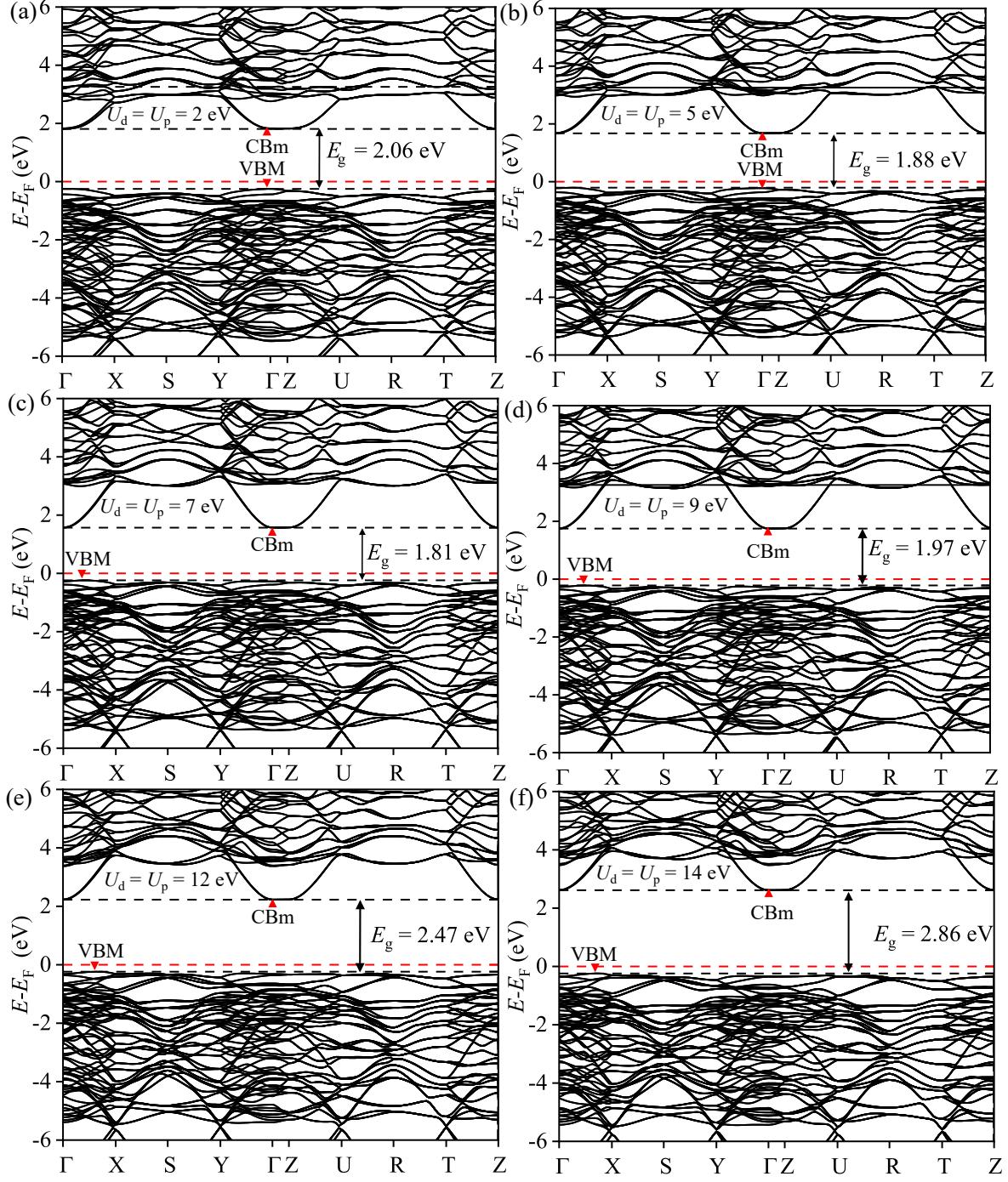


FIG. S6. Electronic BS of BWO in the absence of vdW force for GGA-PBE+ U_d+U_p with (a) $U_d = U_p = 2$ eV, (b) $U_d = U_p = 5$ eV, (c) $U_d = U_p = 7$ eV, (d) $U_d = U_p = 9$ eV, (e) $U_d = U_p = 12$ eV and (f) $U_d = U_p = 14$ eV. The band gap E_g in the BS varies with different values of U_d and U_p .

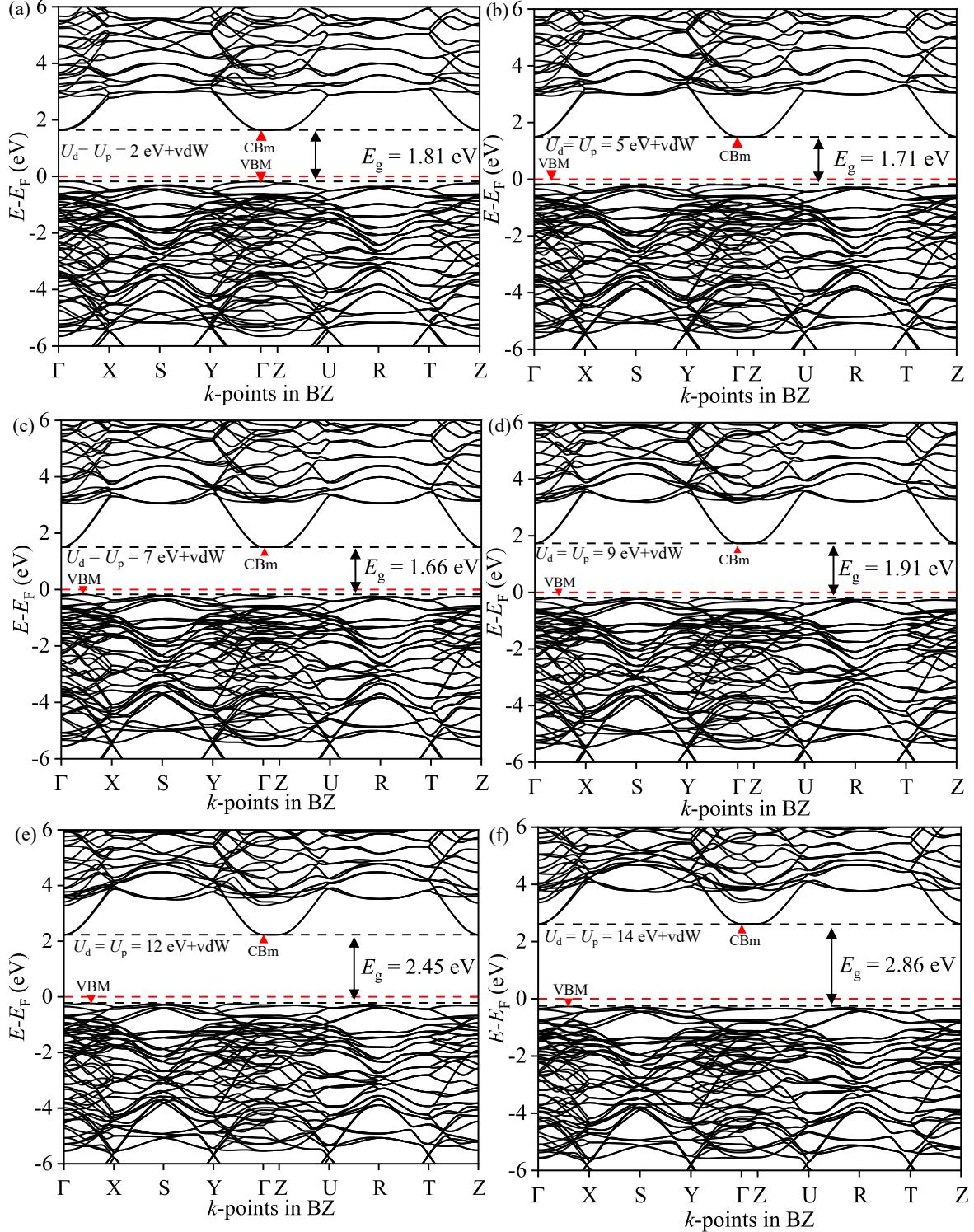


FIG. S7. The vdW force is included. Electronic BS of BWO for GGA-PBE+ $U_d+U_p+\text{vdW}$ with (a) $U_d = U_p = 2 \text{ eV}$, (b) $U_d = U_p = 5 \text{ eV}$, (c) $U_d = U_p = 7 \text{ eV}$, (d) $U_d = U_p = 9 \text{ eV}$, (e) $U_d = U_p = 12 \text{ eV}$ and (f) $U_d = U_p = 14 \text{ eV}$. The band gap E_g in the BS varies with different values of U_d and U_p .

VI. ELASTIC PROPERTIES SIMULATION

TABLE S6. Elastic constants (C_{ij}), bulk moduli (B_V , B_R and B_H), shear moduli (G_V , G_R , G_H), Young's moduli (E_V , E_R , E_H), Poisson's ratio (ν_V , ν_R , ν_H) and Pugh's ratio (k_V , k_R , k_H) in Voigt–Reuss–Hill framework for BWO using GGA-PBE, GGA-PBE+ U_d+U_p and GGA-PBE+ U_d+U_p+vdW .

E.P.	Elastic Properties (E.P.) of BWO		
	GGA-PBE	GGA-PBE+ U_d+U_p	GGA-PBE+ U_d+U_p+vdW
C_{11} (GPa)	131.293	201.29	233.269
C_{12} (GPa)	4.028	68.734	90.058
C_{13} (GPa)	42.544	48.644	58.849
C_{22} (GPa)	103.827	190.576	215.771
C_{23} (GPa)	12.643	8.052	18.775
C_{33} (GPa)	98.635	100.703	106.653
C_{44} (GPa)	44.365	36.669	39.994
C_{55} (GPa)	60.567	70.187	80.6
C_{66} (GPa)	33.829	104.078	106.212
B_V (GPa)	50.240	82.600	99.010
B_R (GPa)	48.632	68.254	78.834
B_H (GPa)	49.438	75.428	88.920
G_V (GPa)	46.050	66.660	71.230
G_R (GPa)	43.064	56.286	60.287
G_H (GPa)	44.559	61.474	65.758
E_V (GPa)	105.830	157.590	172.350
E_R (GPa)	99.749	132.449	144.122
E_H (GPa)	102.794	145.024	158.261
ν_V	0.150	0.180	0.210
ν_R	0.158	0.177	0.195
ν_H	0.153	0.180	0.203
k_V	1.090	1.240	1.390
k_R	1.129	1.213	1.308
k_H	1.109	1.227	1.352

VII. BORN CHARGE

The Born effective charge (BEC) embodies the atomic charge dynamics. The BEC has its origin in the screening of long-range Coulomb potential of the ions whose motion forms the phonon characteristics. The simulated BEC tensor is displayed in Table S7 for both GGA-PBE+vdW and GGA-PBE+ U_d+U_p +vdW.

TABLE S7. Born effective charge tensor of BWO using GGA-PBE+vdW and GGA-PBE+ U_d+U_p +vdW.

	Z _B	Position	xx	xy	xz	yx	yy	yz	zx	zy	zz
BWO	Bi	4a	4.779	-0.263	0.495	-0.201	4.793	0.010	0.907	0.536	4.453
GGA-PBE+vdW	Bi	4a	4.781	0.264	0.493	0.202	4.792	-0.011	0.907	-0.536	4.454
	W	4a	8.196	0.005	0.450	-0.003	6.820	0.001	0.411	0.000	7.989
	O1	4a	-2.207	0.042	1.306	0.301	-2.201	0.639	1.214	1.222	-4.509
	O2	4a	-3.699	-2.142	-0.434	-2.112	-3.039	-0.339	-0.404	-0.254	-1.342
	O3	4a	-3.696	2.143	-0.432	2.112	-3.042	0.340	-0.402	0.256	-1.341
	O4	4a	-2.206	0.041	1.305	0.302	-2.202	0.571	1.212	1.225	-4.509
	O5	4a	-2.974	-0.254	0.452	0.117	-2.961	0.150	0.193	0.218	-2.598
	O6	4a	-2.975	0.253	-0.452	-0.116	-2.961	0.150	-0.193	0.218	-2.598
BWO	Bi	4a	4.791	-0.272	0.620	-0.362	4.736	0.123	1.028	0.385	4.251
GGA-PBE+ U_d+U_p	Bi	4a	4.791	0.272	0.620	0.362	4.735	-0.123	1.028	-0.385	4.251
+vdW	W	4a	8.357	0.002	0.502	-0.002	7.950	0.000	0.573	0.000	8.582
	O1	4a	-2.450	0.160	1.230	0.370	-2.190	0.222	1.262	0.506	-4.382
	O2	4a	-3.560	-2.058	-0.134	-2.187	-3.527	-0.099	-0.075	0.005	-1.657
	O3	4a	-3.560	2.058	-0.134	2.187	-3.528	0.173	-0.075	-0.004	-1.657
	O4	4a	-2.450	0.160	1.230	0.370	-2.190	0.223	1.262	0.506	-4.383
	O5	4a	-2.960	-0.320	0.405	0.256	-2.993	0.249	0.130	0.276	-2.502
	O6	4a	-2.959	0.320	-0.405	-0.256	-2.993	0.249	-0.130	0.276	-2.502